SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 100 V Forward Current - 8 A

Features

- Schottky barrier chip
- Guard ring die construction for transient protection
- High surge capability
- Low power loss, high efficiency
- High current capability, Low forward voltage drop
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

Mechanical Data

- Case: Molded plastic, TO-220A
- Epoxy: UL 94V-0 rate flame retardant
- Terminals: Leads solderable per MIL-STD-202, Method 208 guaranteed
- Polarity: As marked
- Mounting position: Any

Maximum Ratings and Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load, For capacitive load, derate current by 20%.

Parameter	Symbols	SR8100	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	100	V
Maximum RMS Voltage	V _{RMS}	70	V
Maximum DC Blocking Voltage	V _{DC}	100	V
Maximum Average Forward Rectified Current at $T_C = 25 ^{\circ}C$	I _{F(AV)}	8	А
Non-Repetitive Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	150	А
Maximum Forward Voltage at 8 A and $T_C = 25 ^{\circ}C$	V _F	0.72	V
$\label{eq:maximum} \begin{array}{ll} \mbox{Maximum Reverse Current Rated DC Blocking Voltage} & \mbox{at } T_{C} = 25^{\circ}\mbox{C} \\ & \mbox{at } T_{C} = 125^{\circ}\mbox{C} \end{array}$	I _R	0.55 7	mA
Typical Junction Capacitance ¹⁾	CJ	350	pF
Typical Thermal Resistance Junction to Case ²⁾	R _{θJC}	2	K/W
Operating Temperature Range	TJ	- 55 to + 150	°C
Storage Temperature Range	T _{stg}	- 55 to + 175	°C

¹⁾ Measured at 1 MHz and applied reverse voltage of 4 V.

²⁾ Thermal Resistance from Junction to case mounted on heatsink.







